

# **HAT2220R**

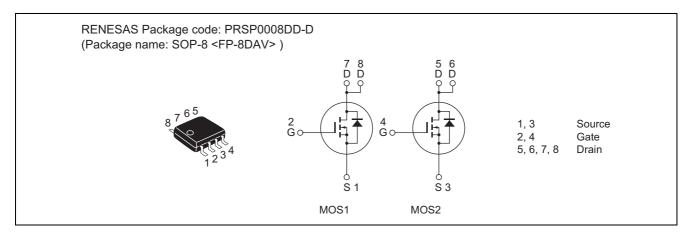
# Silicon N Channel MOS FET High Speed Power Switching

REJ03G1572-0500 Rev.5.00 Jul 20, 2007

#### **Features**

- Low on-resistance
- Low drive current
- High density mounting

#### **Outline**



## **Absolute Maximum Ratings**

 $(Ta = 25^{\circ}C)$ 

Item	Symbol	Ratings	Unit
Drain to source voltage	$V_{DSS}$	450	V
Gate to source voltage	$V_{GSS}$	±30	V
Drain current	I <sub>D</sub> Note1	0.7	А
Drain peak current	I <sub>D(pulse)</sub> Note2	2.1	А
Body-drain diode reverse drain current	I <sub>DR</sub>	0.7	Α
Avalanche current	I <sub>AP</sub> Note3	0.7	Α
Channel dissipation	Pch Note4	2	W
Channel dissipation	Pch Note5	3	W
Channel temperature	Tch	150	°C
Storage temperature	Tstg	-55 to +150	°C

Notes: 1.  $PW \le 1 s$ 

2. PW  $\leq$  10  $\mu$ s, duty cycle  $\leq$  1%

3. STch = 25 °C, Tch  $\leq$  150 °C

4. 1 Drive operation : When using the glass epoxy board (FR4 40 x 40 x 1.6 mm), PW  $\leq$  10 s

5. 2 Drive operation: When using the glass epoxy board (FR4 40 x 40 x 1.6 mm), PW  $\leq$  10 s

## **Electrical Characteristics**

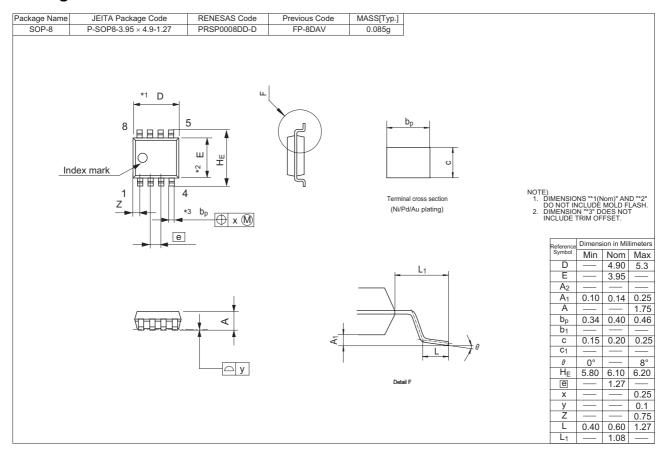
 $(Ta = 25^{\circ}C)$ 

Item	Symbol	Min	Тур	Max	Unit	Test Conditions
Drain to source breakdown voltage	$V_{(BR)DSS}$	450	_	_	V	$I_D = 10 \text{ mA}, V_{GS} = 0$
Zero gate voltage drain current	I <sub>DSS</sub>		_	1	μΑ	$V_{DS} = 450 \text{ V}, V_{GS} = 0$
Gate to source leak current	I <sub>GSS</sub>	1	_	±0.1	μΑ	$V_{GS} = \pm 30 \text{ V}, V_{DS} = 0$
Gate to source cutoff voltage	$V_{GS(off)}$	3.0	_	4.5	V	$V_{DS} = 10 \text{ V}, I_{D} = 1 \text{ mA}$
Forward transfer admittance	y <sub>fs</sub>	0.55	0.95	_	S	$I_D = 0.4 \text{ A}, V_{DS} = 10 \text{ V}^{\text{Note6}}$
Static drain to source on state	R <sub>DS(on)</sub>	_	5.5	6.5	Ω	$I_D = 0.4 \text{ A}, V_{GS} = 10 \text{ V}^{\text{Note6}}$
resistance						
Input capacitance	Ciss		140	_	pF	V <sub>DS</sub> = 25 V
Output capacitance	Coss	_	17	_	pF	$V_{GS} = 0$
Reverse transfer capacitance	Crss	_	5	_	pF	f = 1 MHz
Turn-on delay time	t <sub>d(on)</sub>	_	22	_	ns	I <sub>D</sub> = 0.4 A
Rise time	t <sub>r</sub>	_	12	_	ns	V <sub>GS</sub> = 10 V
Turn-off delay time	$t_{d(off)}$	_	38	_	ns	$R_L = 562 \Omega$
Fall time	t <sub>f</sub>	_	47	_	ns	$Rg = 10 \Omega$
Total gate charge	Qg	_	4.9	_	nC	V <sub>DD</sub> = 360 V
Gate to source charge	Qgs	_	0.6	_	nC	V <sub>GS</sub> = 10 V
Gate to drain charge	Qgd	_	3.2	_	nC	$I_D = 0.7 A$
Body-drain diode forward voltage	$V_{DF}$		0.84	1.24	V	$I_F = 0.7 \text{ A}, V_{GS} = 0^{\text{Note6}}$
Body-drain diode reverse recovery	t <sub>rr</sub>	_	120	_	ns	$I_F = 0.7 \text{ A}, V_{GS} = 0$
time						$di_F/dt = 100 \text{ A/ } \mu\text{s}$

Notes: 6. Pulse test

7. Since this device includes two high voltage Power MOS FET chips (V<sub>DSS</sub> ≥ 450 V), high voltage margin may occur. (Between No.6 pin and No.7 pin in the outline fig.) Therefore, please be sure to confirm about Electric discharge between No.6 pin and No.7 pin in the equivalent circuit.

## **Package Dimensions**



# **Ordering Information**

Part No.	Quantity	Shipping Container
HAT2220R-EL-E	2500 pcs	Taping

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